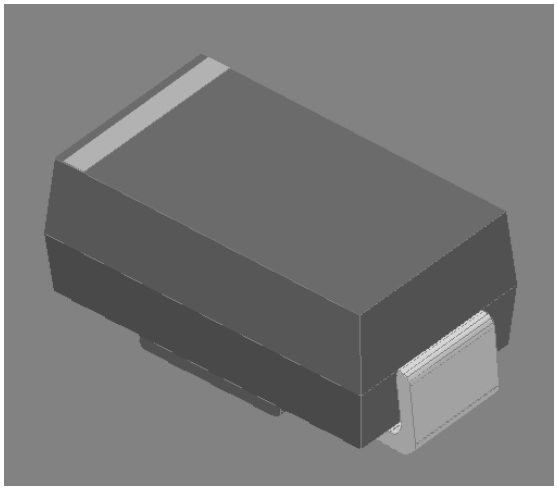
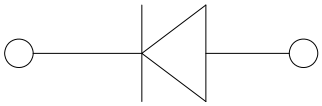
RoHS
COMPLIANT



- Low profile package
- Ideal for automated placement
- Glass passivated chip junction
- High forward surge capability
- Super Fast reverse recovery time
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

For use in high frequency rectification of power supplies, inverters, converters, and freewheeling diodes for consumer, and telecommunication.



- : DO-214AC(SMA)
  Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- : Tin plated leads, solderable per J-STD-002 and JESD22-B102
- Cathode line denotes the cathode end

■ (T_a=25 Unless otherwise specified

Device marking code			MURS220A	MURS240A	MURS260A
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	V	200	400	600
Maximum RMS Voltage	V_{RMS}	V	140	280	420
Maximum DC blocking Voltage	V_{DC}	V	200	400	600
Average rectified output current @60Hz sine wave, resistance load, TL (Fig.1)	I_O	A	2.0		
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave,1 cycle, Tj=25	I_{FSM}	A	50		
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Tj=25			100		
Current squared time @1ms≤t≤8.3ms Tj=25	I^2t	A^2s	10.375		
Storage temperature	T_{stg}		-55 ~ +150		
Junction temperature	T_j		-55 ~ +150		

■ Ta=25 Unless otherwise specified

Maximum instantaneous forward voltage	V_F	V	I_{FM}=2.0A	0.92	1.25	
Maximum reverse recovery time	t_{rr}	ns	I_F=0.5A,I_R=1.0A, I_{rr}=0.25A	25	50	
Maximum DC reverse current at rated DC blocking voltage	I_R	μA	T_j=25	5.0		
			T_j=125	50		
Typical junction capacitance	Cj	pF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	25	25	24

■

◆

Reverse Recovery Time	T_{RR}	ns	Tj=25	I_F=1A di/dt=-50A/us V_{RM}=30V	-	26	-
			Tj=25	I_F=2A di/dt=-200A/us V_{RM}=100V	-	23	-
			Tj=125		-	30	-
Peak recovery current	I_{RRM}	A	Tj=25		-	3.1	-
			Tj=125		-	5.0	-
Reverse recovery charge	Qrr	nC	Tj=25		-	35.4	-
			Tj=125		-	73.8	-
Non-repetitive avalanche energy	E_{AS}	mJ	Tj=25	I_R=1.8 A L=15 mH	24.3	-	-

◆

Reverse Recovery Time	T_{RR}	ns	Tj=25	I_F=1A di/dt=-50A/us V_{RM}=30V	-	35	-
			Tj=25	I_F=2A di/dt=-200A/us V_{RM}=200V	-	30	-
			Tj=125		-	45	-
Peak recovery current	I_{RRM}	A	Tj=25		-	3.7	-
			Tj=125		-	5.8	-
Reverse recovery charge	Qrr	nC	Tj=25		-	55.4	-
			Tj=125		-	130.6	-
Non-repetitive avalanche energy	E_{AS}	mJ	Tj=25	I_R=0.5A L=15 mH	1.9	-	-

◆

Reverse Recovery Time	T_{RR}	ns	Tj=25	I_F=1A di/dt=-50A/us V_{RM}=30V	-	50	-
			Tj=25	I_F=2A di/dt=-200A/us V_{RM}=400V	-	43	-
			Tj=125		-	66	-
Peak recovery current	I_{RRM}	A	Tj=25		-	5.0	-
			Tj=125		-	7.4	-
Reverse recovery charge	Qrr	nC	Tj=25		-	105.9	-
			Tj=125		-	243.8	-
Non-repetitive avalanche energy	E_{AS}	mJ	Tj=25	I_R=0.5A L=15 mH	1.9	-	-

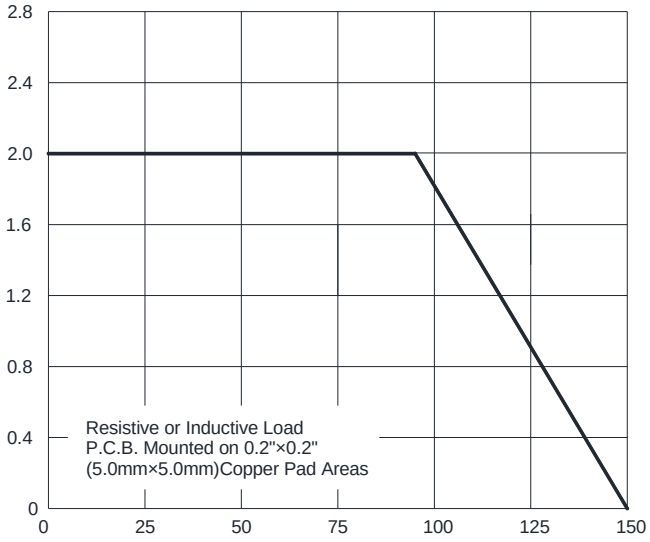
■ Ta=25 Unless otherwise specified

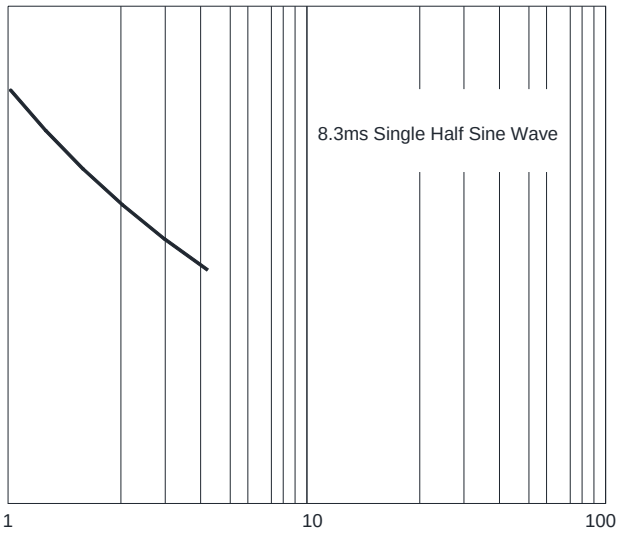
Typical Thermal resistance	$R_{\theta J-A}$(1)	/W	65		
	$R_{\theta J-L}$(1)		25		
	$R_{\theta J-C}$(1)		20		

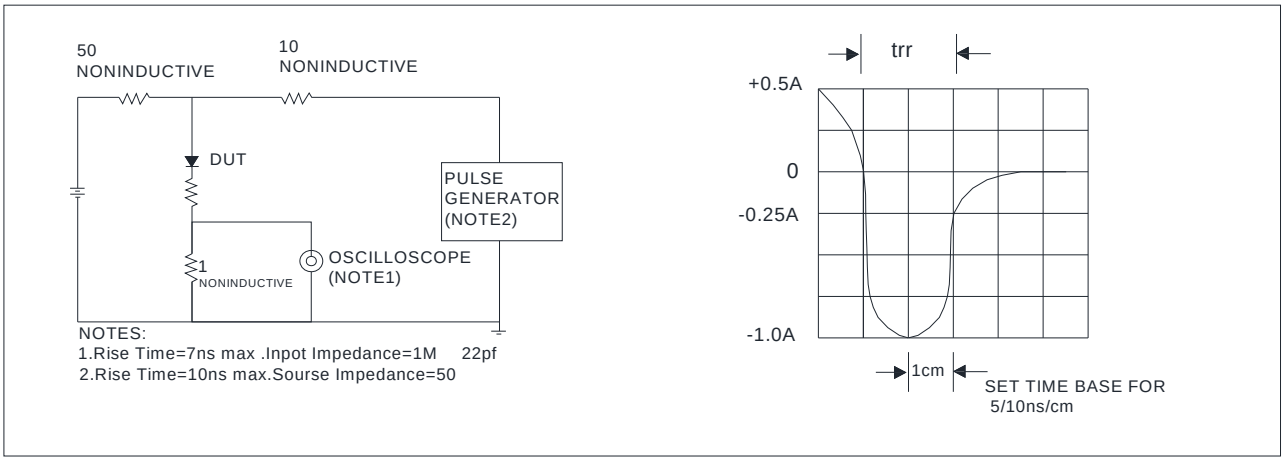
Note:

(1) Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas

■ (Typical)


2.8
2.4
2.0
1.6
1.2
0.8
0.4
0
0
25
50
75
100
125
150
Resistive or Inductive Load
P.C.B. Mounted on 0.2"×0.2"
(5.0mm×5.0mm)Copper Pad Areas


8.3ms Single Half Sine Wave
1
10
100


50
NONINDUCTIVE
10
NONINDUCTIVE
DUT
PULSE
GENERATOR
(NOTE2)
1
NONINDUCTIVE
OSCILLOSCOPE
(NOTE1)
NOTES:
1.Rise Time=7ns max .Inpot Impedance=1M 22pf
2.Rise Time=10ns max.Sourse Impedance=50
trr
+0.5A
0
-0.25A
-1.0A
1cm
SET TIME BASE FOR
5/10ns/cm

■ (Example)

MURS220A-MURS260A	F1	Approximate 0.059	5000	/	80000	13” reel
MURS220A-MURS260A	F2	Approximate 0.059	7500	/	120000	13” reel
MURS220A-MURS260A	F3	Approximate 0.059	7500	/	60000	13” reel
MURS220A-MURS260A	F4	Approximate 0.059	1800	14400	57600	7” reel
MURS220A-MURS260A	F5	Approximate 0.059	2000	16000	64000	7” reel
MURS220A-MURS260A	F6	Approximate 0.059	5000	/	100000	13” reel

■

Dim	Min	Max
A	1.25	1.58
B	2.40	2.83
C	4.00	4.75
D	1.90	2.30
E	4.93	5.28
F	0.76	1.41
G	0.05	0.20
H	0.15	0.31
I	1.70	2.10



Dim	Millimeters
P1	4.00
P2	1.50
P3	6.50
Q1	2.50
Q2	1.70

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the